**Product data sheet** 





### 1. Product profile

#### 1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

#### **1.2 Features and benefits**

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability

#### **1.3 Applications**

- General purpose low power motor control
- Home appliances

#### **1.4 Quick reference data**

#### Table 1. Quick reference data

Symbol Parameter Conditions Min Тур Max Unit V<sub>DRM</sub> repetitive peak off-state 800 V voltage I<sub>TSM</sub> non-repetitive peak full sine wave;  $T_{j(init)} = 25 \text{ °C};$ 12.5 A on-state current  $t_p = 20 \text{ ms}; \text{ see Figure 4};$ see Figure 5 I<sub>T(RMS)</sub> RMS on-state current full sine wave;  $T_{lead} \le 45 \text{ °C}$ ; 1 А see Figure 1; see Figure 3; see Figure 2



- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants
- Industrial process control
- Low power AC Fan controllers

4Q Triac

Table 1.	Quick reference	data	continued

Parameter	Conditions	Min	Тур	Max	Unit
aracteristics					
I <sub>GT</sub> gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{T2+ G+};$ $T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure 7}}{2}$	0.4	-	10	mA
	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 ^\circ\text{C}; \text{ see } \frac{\text{Figure 7}}{100000000000000000000000000000000000$	0.4	-	10	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^\circ\text{C}; \text{ see } \frac{\text{Figure 7}}{100000000000000000000000000000000000$	0.4	-	10	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^\circ\text{C}; \text{ see } \frac{\text{Figure 7}}{100000000000000000000000000000000000$	0.4	-	10	mA
	aracteristics	$\label{eq:aracteristics} \begin{tabular}{lllllllllllllllllllllllllllllllllll$	aracteristics       V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; 0.4 $T_j = 25 \text{ °C}$ ; see Figure 7       V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; 0.4 $V_D = 12 \text{ V}$ ; I <sub>T</sub> = 0.1 A; T2+ G-; 0.4 $T_j = 25 \text{ °C}$ ; see Figure 7 $V_D = 12 \text{ V}$ ; I <sub>T</sub> = 0.1 A; T2- G-; 0.4 $T_j = 25 \text{ °C}$ ; see Figure 7 $V_D = 12 \text{ V}$ ; I <sub>T</sub> = 0.1 A; T2- G-; 0.4 $T_j = 25 \text{ °C}$ ; see Figure 7 $V_D = 12 \text{ V}$ ; I <sub>T</sub> = 0.1 A; T2- G-; 0.4 $T_j = 25 \text{ °C}$ ; see Figure 7 $V_D = 12 \text{ V}$ ; I <sub>T</sub> = 0.1 A; T2- G+; 0.4	$ \begin{array}{c} \text{aracteristics} \\ \\ \text{gate trigger current} \\ & \begin{array}{c} V_D = 12 \ \text{V;} \ \text{I}_T = 0.1 \ \text{A;} \ \text{T2+G+;} \\ T_j = 25 \ ^\circ\text{C;} \ \text{see} \ \underline{\text{Figure 7}} \\ \hline V_D = 12 \ \text{V;} \ \text{I}_T = 0.1 \ \text{A;} \ \text{T2+G-;} \\ T_j = 25 \ ^\circ\text{C;} \ \text{see} \ \underline{\text{Figure 7}} \\ \hline V_D = 12 \ \text{V;} \ \text{I}_T = 0.1 \ \text{A;} \ \text{T2-G-;} \\ \hline V_D = 12 \ \text{V;} \ \text{I}_T = 0.1 \ \text{A;} \ \text{T2-G+;} \\ \hline V_D = 12 \ \text{V;} \ \text{I}_T = 0.1 \ \text{A;} \ \text{T2-G+;} \\ \hline V_D = 12 \ \text{V;} \ \text{I}_T = 0.1 \ \text{A;} \ \text{T2-G+;} \\ \hline \end{array} \right. $	$ \begin{array}{c} \text{aracteristics} \\ \hline \\ \text{gate trigger current} \\ \hline \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 + \text{G+;} \\ T_j = 25 \ ^\circ \text{C; see } \underline{Figure 7} \\ \hline \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 + \text{G-;} \\ T_j = 25 \ ^\circ \text{C; see } \underline{Figure 7} \\ \hline \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 - \text{G-;} \\ \hline \\ T_j = 25 \ ^\circ \text{C; see } \underline{Figure 7} \\ \hline \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 - \text{G-;} \\ \hline \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 - \text{G-;} \\ \hline \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 - \text{G-;} \\ \hline \end{array} $

## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		NI
2	G	gate		T2-T1
3	T1	main terminal 1		`G sym051
			SOT54 (TO-92)	

## 3. Ordering information

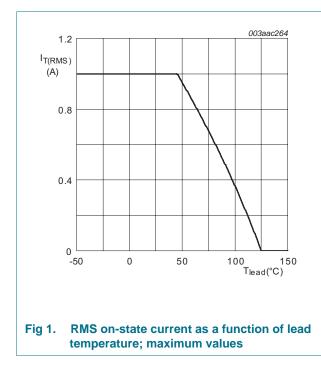
Table 3. Ordering in	nformation		
Type number	Package		
	Name	Description	Version
Z0109NA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

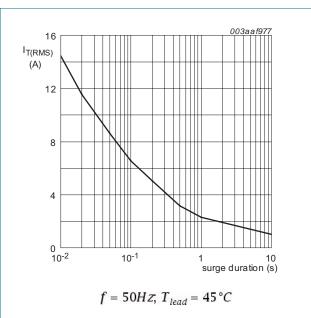
## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 45 °C; see <u>Figure 1;</u> see <u>Figure 3</u> ; see <u>Figure 2</u>	-	1	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	12.5	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	13.8	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	0.78	A <sup>2</sup> s
dI <sub>T</sub> /dt rate of rise of on-state current	rate of rise of on-state current	I <sub>T</sub> = 1 A; I <sub>G</sub> = 20 mA; dI <sub>G</sub> /dt = 100 mA/µs; T2+ G+	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/µs; T2+ G-	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/µs; T2- G-	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/µs; T2- G+	-	20	A/µs
I <sub>GM</sub>	peak gate current		-	1	А
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>i</sub>	junction temperature		-	125	°C

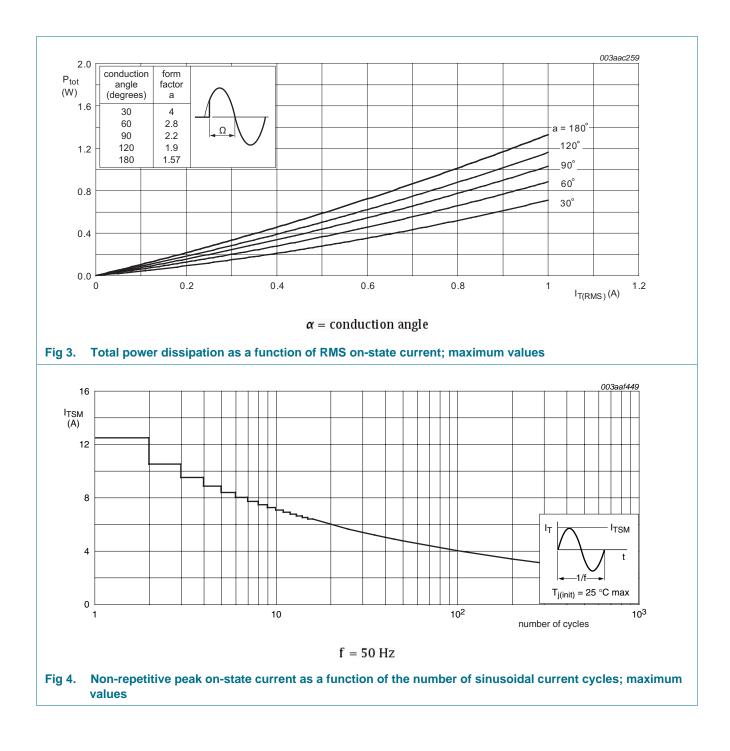






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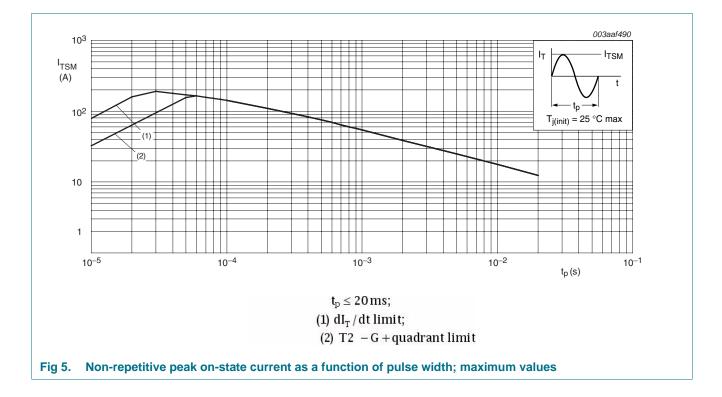
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## **Z0109NA0**

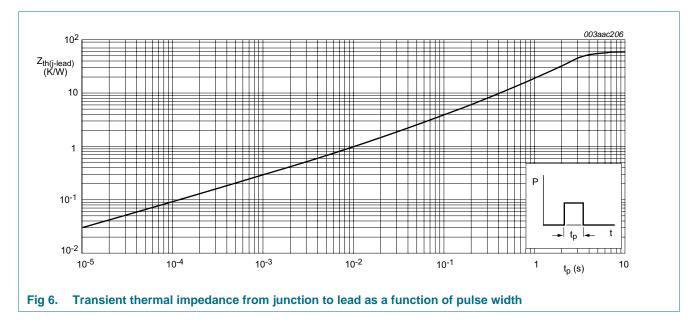
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### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; see <u>Figure 6</u>	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm	-	150	-	K/W



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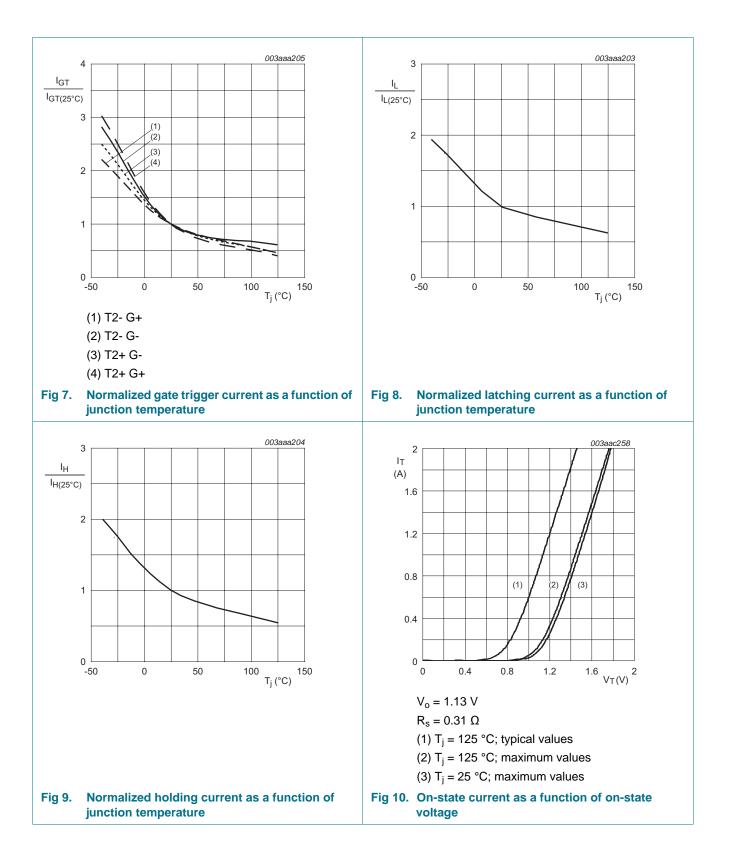
### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G+}; \text{T}_j = 25 \text{ °C};$ see Figure 7	0.4	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	0.4	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	0.4	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G+}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	0.4	-	10	mA
I <sub>L</sub> latching c	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G+; T}_j = 25 \text{ °C};$ see Figure 8	-	-	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	15	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{1000 \text{ Figure 9}}$	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	-	1.3	V
		V <sub>D</sub> = 800 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; see <u>Figure 11</u>	0.2	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 110 °C; gate open circuit; exponential waveform; see <u>Figure 12</u>	120	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; \text{ T}_j = 110 \text{ °C};$ dl <sub>com</sub> /dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

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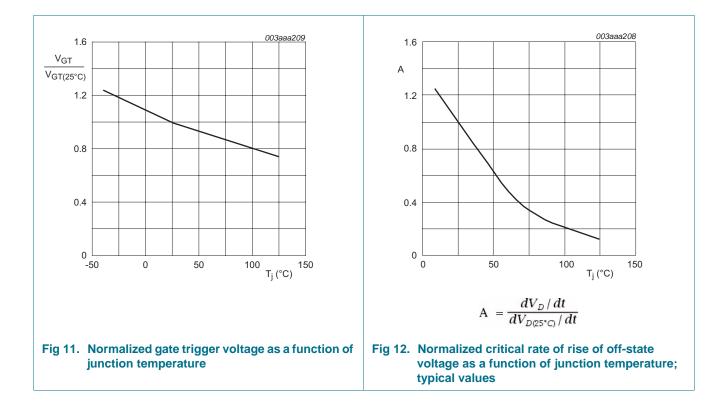
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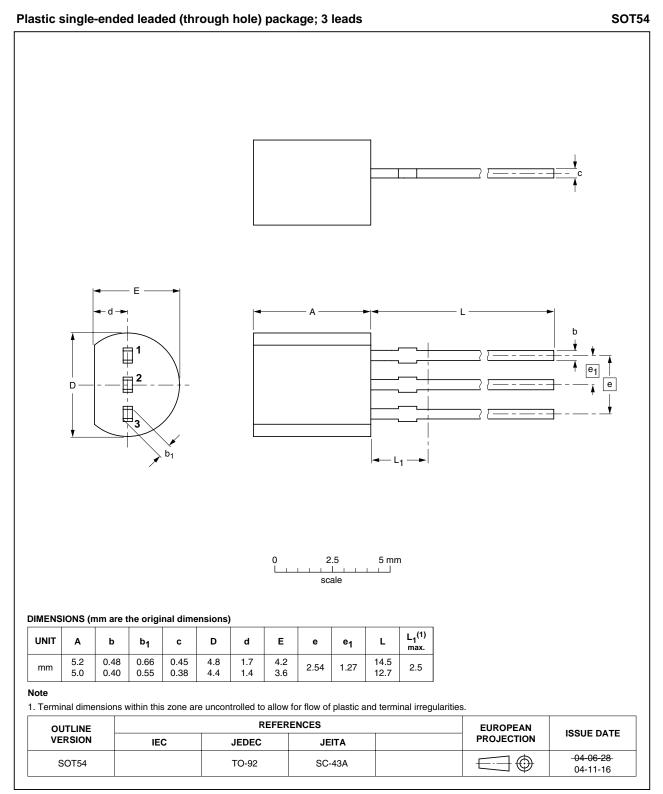
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### 7. Package outline

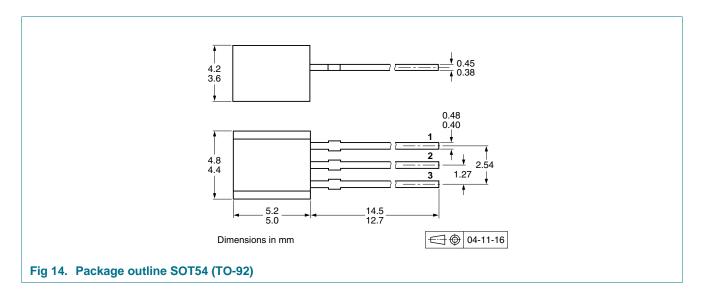


#### Fig 13. Package outline SOT54 (TO-92)

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## 8. Package outline



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## 9. Revision history

Table 7. Revisio	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0109NA0 v.3	20110512	Product data sheet	-	Z0109NA0 v.2
Modifications:	<ul> <li>Various chan</li> </ul>	ges to content.		
Z0109NA0 v.2	20110318	Product data sheet	-	Z0109NA0 v.1

#### **10. Legal information**

#### **10.1** Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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of the device.

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